First principle calculations of conductance within plane wave basis set via nonorthogonal W annier-type atom ic orbitals

Zhenyu Li and D.S.Kosov

Departm ent of Chem istry and Biochem istry, University of Maryland, College Park, 20742, USA

W e present a plane wave/pseudopotential im plem entation of the m ethod to calculate electron transport properties of nanostructures. The conductance is calculated via the Landauer form ula within form alism of G reen's functions. N onorthogonal W annier-type atom ic orbitals are obtained by the sequential unitary rotations of virtual and occupied K ohn-Sham orbitals, which is followed by two-step variational localization. W e use these non-orthogonal W annier type atom ic orbitals to partition the K ohn-Sham H am iltonian into electrode-contact-electrode submatrices. The electrode parts of the system are modeled by two m etal clusters with additional Lorentzian broadening of discrete energy levels. W e exam ined our im plem entation by m odeling the transport properties of N a atom ic wires. O ur results indicate that with the appropriate level broadening the sm all cluster m odel for contacts reproduces odd-even oscillations of the conductance as a function of the nanow ire length.

I. IN TRODUCTION

The last decade has witnessed a remarkable miniaturization of conventional m icroelectronic devices. If this trend is to continue, elem ents of microelectronic circuits, e.g. transistors and contacts, will soon shrink to the size of a single molecule. One of the major goals in nanotechnology is the construction, measurement and modeling of electronic circuits in which molecular system s act as conducting elements¹. A courate and reproducible m easurem ents of current-voltage characteristics have been recently reported for atom ic wires and single m olecules^{2,3,4}. The experim ental progress has been accompanied by considerable advances towards density functional theory based calculations of transport properties of nanostructures. This activity has been largely spurred on by developm ent of several electronic structure codes for the st principle transport calculations.^{5,6,7,8}

The prerequisite for non-equilibrium G reen's function calculation of conductance is the partitioning of the K ohn-Sham (K S) H am iltonian into left/right electrodes and contact regions. Such partitioning is straightforw and if one expands the K S wavefunctions as liner com binations of atom ic orbitals^{5,6,7,8} but it becomes a form idable theoretical problem if the plane waves are used for a representation of the K S orbitals. One of the aim s of this paper is development of a theoretical scheme to the partition of the K S H am iltonian within plane wave basis set.

It has been recently proposed that W annier functions can be used to link plane wave electronic structure and G reen's function transport calculations.^{9,10} W annier functions are localized in coordinate space and are obtained by an unitary transformation of the KS orbitals. The number of W annier functions is typically much smaller than the dimension of G aussian-type basis sets. The additional advantage is that, we treat the electrode and the wire at the same level of theory within the W annier functions basis whereas it is not possible if one uses G aussian basis set. The quality of G aussiantype atom ic basis set can not be easily controlled, which makes the results of calculation sensitive to a particular choice of basis functions. In principle, these problems do not exist for plane wave basis set, where its quality is simply controlled by a single parameter, the cuto energy.¹¹ By increasing the cuto energy, we can always get converged results. There are two disadvantages which makes standard W annier functions inapplicable for the calculations of transport properties. First, W annier functions are de ned for occupied KS orbitals and if the same localization scheme is directly used for the virtual orbitals it typically leaves them as delocalized as they were before the unitary transform ation. Second, the centers of these localized W annier functions are not controllable before minimization. To address both issues, we have developed the localization technique which yields non-orthogonalW annier-type atom ic orbitals (NOWAOs) from the plane-wave based KS orbitals. NOW AOs are the maxim ally localized functions de ned via the set of unitary transform ations of occupied and virtual KS orbitals. Our scheme is based upon the combination of two localization techniques: Thygesen-Hansen-Jacobsen partially occupied W annier functions¹² and M ortensen-P arrinello non-orthogonal localization.¹³ C om bined together, these two techniques are used to include the virtual KS orbitals and to shift the W annier centers from bonds to atom s.

O ne additional ingredient, which is necessary for calculations of conductance, is the G reen's function of the electrodes. In this paper, we represent the leads by two sm all clusters with additional Lorentzian broadening of the energy levels.

W e have in plem ented the working equations within a plane-wave/pseudopotential code¹⁴ and we will dem onstrate the num erical accuracy of im plem entation for som e prototypical test exam ples. The rem ainder of the paper is organized as follows. In Section II, we describe the details of ourm ethod to calculate the conductance of nanostructures, and it application to sodium atom ic wires is given in Section III. In Section IV, we conclude the paper.

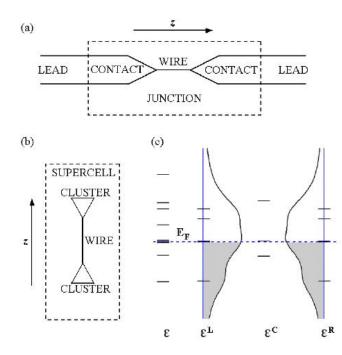


FIG.1: (a) Schem atic representation of an atom ic/m olecular scale junction system for electronic transportation. (b) Simpli ed transportation m odel used in our m ethod. (c) Energy levels for junction system containing three-atom sodium w ire. D ensity of states obtained by Lorentzian broadening of the electrode levels are also shown. See text for details.

II. M ETHOD

A. Partitioning of the Ham iltonian

W e begin with the K ohn-Sham equation for the entire nanow ire junction

$$H j_{i} = E_{i} j_{i}; \qquad (1)$$

where H is the Kohn-Sham Ham iltonian and j_i is the Kohn-Sham orbital. The next step is the partitioning of the system into three parts: two electrodes and wire (typically atom icorm olecularwire plus parts of the lead) as it is shown in Fig. 1. The partitioning of the system results into the partitioning of the Ham iltonian to seven sub-matrices (left lead, contact, right lead and the lead-wire interactions) and it is perform ed by transform ing the representation of the KS Ham iltonian from KS orbitals to atom ically localized basis sets:

$$j_{i}i = \bigcup_{n=1}^{X} U_{in} j_{N_{n}}i; \qquad (2)$$

where U_{in} is a unitary transformation and $jw_n i$ form atom ically localized complete basis set. The unitary transformation U_{in} is applied to the KS Ham iltonian

$$H = j_{i} i E_{i} h_{i} j = j_{w_{n}} i H_{nm} h_{w_{m}} j \quad (3)$$

with

$$H_{nm} = \bigcup_{\substack{n \ i}} U_{n \ i} E_{i} U_{im}$$
(4)

and yields the partitioning of the Hamiltonian into electrode wire-electrode sub-matrices:

If the basis set $j!_n i$ is not orthogonal, the analogous partitioning should be performed for the overlap matrix S $(S_{m n} = h!_m j!_n i)$. Matrices H and S can be de nited if indexes n and and m in H_{nm} (3) are associated with the atom ic positions. But this is not the case when periodic boundary conditions are employed and the KS orbitals are expanded in plane waves:

$$I_{i}(\mathbf{r}) = \frac{1}{\mathbf{p} - \frac{1}{cell}} \operatorname{C}_{iG} \exp(iG \mathbf{r}); \quad (6)$$

where C_{iG} are the expansion coe cients. The plane waves exp (iG r) do not have any reference to the atom ic positions and therefore the partitioning of the K S H am iltonian into electrode wire-electrode subspaces can not be performed directly within the plane wave representation. Several groups have attempted to overcom e this di culty by W annier function representations of the K S orbitals.^{9,10}

B. Non-orthogonal W annier-type A tom ic O rbitals

W annier functions are localized functions which span the same space as the eigenstates of a band or a group of bands. Traditional W annier functions are obtained by transform ing B loch representation to real space representation,¹⁵ in which B loch vector K is substituted by the lattice vector R of the unit cell where the orbital is localized.

$$f(n) = \frac{2}{(2)^{3}} \int_{R_{K}} j_{nk} i e^{i n (k) i k R} dk$$
$$= \frac{2}{(2)^{3}} \int_{R_{Z}} U_{mn}^{(k)} j_{mk} i e^{i k R} dk \qquad (7)$$

where $U_{mn}^{(k)}$ is an arbitrary unitary matrix. The integration in eq.(7) is done in reciprocal space within the whole B rillouin zone. The vector \tilde{k} equals zero for disordered systems like nanostructures or molecular wire junctions. In this case, the W annier functions is de ned via the unitary transform ation of the KS orbitals¹⁶

$$j!_{n}i = U_{m}nj_{m}i: \qquad (8)$$

There are several di erent schem es to de ne unitary matrix $U_{m\,n}$ and the choice the unitary transform ation can be tailored to particular applications. Finding the maximally localized W annier functions is pivotal for the partitioning of the Ham iltonian. A lthough there are several possible ways to de ne maximally localized W annier functions, the method of minimization of the mean square spread stands out.^{17,18}

W annier functions are traditionally constructed only from the occupied KS orbitals. Occupied W annier functions are located on the chem icalbonds, which som etim es makes the partition of junction systems di cult. The additional complication is that the sum in eq.(3) runs over all KS orbitals (occupied and virtual) and due to the completeness requirement it is necessary to include as many virtual KS orbitals in the consideration as possible. Therefore, to be used in transport calculations W annier functions should be constructed in such a way that (a) they are atom ically localized and (b) they include both occupied and virtualKS orbitals. The above two requirem ents are interconnected since to get atom ic centered W annier functions, we must anyway combine unoccupied anti-bonding states with occupied bonding states. The extraction of anti-bonding states from the entire set of virtual orbitals is di cult com putational problem, since unoccupied anti-bonding states arem ixed with som e scattering states originating from periodic boundary conditions.

Follow ing Thygensen, Hansen and Jacobsen¹² we begin the localization of the KS eigenstates by constructing the linear combination of the virtual orbitals

$$j_{1}i = c_{m 1}j_{M + m}i;$$
 (9)

where N is the number of KS orbitals and M is the number of occupied states. Partially occupied W annier functions are written as 12

$$j_{n}^{*}i = \begin{array}{c} X^{M} & X^{L} \\ U_{m n} j_{m} i + U_{M + 1;n} j_{1}i; \\ m = 1 & l = 1 \end{array}$$
(10)

with L being the number of unoccupied anti-bonding states. The optimal value of L is yet to be determined.

W e m in im ize the follow ing localization functional

$$= \prod_{n}^{X} [h_{n}^{n} j z^{2} j_{n}^{n} i h_{n}^{n} j z j_{n}^{n} i^{2}]$$
(11)

to choose a suitable unitary transform ation $U_{m\,n}$ and to obtain the maximally-localized W annier functions.^{17,18} M inimization of functional is equivalent to maximization of the functional

where $m a trix Z^{I}$ is de ned as

$$Z_{mn}^{I} = h_{m}^{\sim} \dot{p}^{iG_{I}} j_{n}^{\prime} \dot{i}; \qquad (13)$$

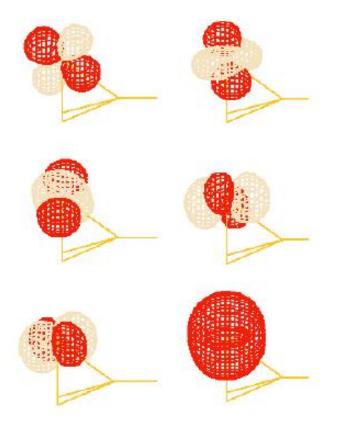


FIG.2: (Coloronline) Non-orthogonalW annier-type atom ic basis functions (NOWAOs) for one gold atom in a simple gold junction system. Only half of the junction is shown.

with G_{I} and w_{I} being the reciprocal lattice vectors and corresponding weights.¹⁶ For simple orthorhom bic supercell, I ranges from 1 to 3, corresponding to x, y, and z. In practical in plem entation, Z^{I} is calculated by $Z^{I} = U \,^{y}Z_{0}^{I}U$, with Z_{0}^{I} de ned as

$$(\mathbb{Z}_{0}^{\mathrm{I}})_{\mathrm{m}\,\mathrm{n}} = \mathrm{h}_{\mathrm{m}} \, \mathbf{\dot{g}} \, {}^{\mathrm{i}\,\mathcal{G}_{\mathrm{I}}} \, {}^{\mathfrak{x}} \mathbf{\dot{j}}_{\mathrm{n}} \mathbf{\dot{i}} \, \mathbf{\dot{i}} \, \tag{14}$$

A nalytical gradients of functional (12) are necessary to perform e ective maximization. If we write the unitary matrix at iteration i as $U_i = U_{i1} \exp(A)$, then the gradients of functional with respect to A can be approximated as

$$(d = dA)_{ij} = \begin{bmatrix} X \\ w_{I} [Z_{ji} (Z_{jj} \ Z_{ii}) \ Z_{ij} (Z_{ii} \ Z_{jj})]: \\ I \end{bmatrix}$$
(15)

The gradient with respect to the coe cient matrix $c_{\rm im}$ is computed by the following form $u\,la^{12}$

$$\begin{array}{l} (d = dc)_{ij} = (16) \\ X \\ w_{I} [\mathbb{Z}_{0} \mathcal{U} \operatorname{diag}(\mathbb{Z}^{y}) + \mathbb{Z}_{0}^{y} \mathcal{U} \operatorname{diag}(\mathbb{Z})] U^{y}]_{N + i; N + j}; \\ \end{array}$$

where diag(Z) is the diagonal part of matrix Z, and U is the rotation matrix from KS orbitals to partly occupied

W annier functions with dimension N (M + L). The orthonom ality constraint on matrix c is invoked through a set of Lagrange multipliers. The steepest descent method is used to maximize . A fler the maximization, the unoccupied anti-bonding states are obtained from the coefcient matrix c through Eq.(9).

A nal set NOW AOs is computed via the additional rotation of partially occupied W annier functions (10):

$$j!_{n} i = \bigvee_{\substack{MX^{+ L} \\ m = 1}} V_{m n} j_{m}^{\sim} i: \qquad (17)$$

Rotation matrix V_{nm} is dened by minimizing the following function¹³ independently for each n:

$$n = h!_{n} \dot{p} (r R_{n}) j!_{n} \dot{i}$$
(18)

The weight function $p(\mathbf{r})$ is chosen in such a way that it has a minimum at r = 0 to localize each $j!_n >$ around \Re_n . Following M ortensen and P arrinello¹³ we select function $p(\mathbf{r})$ as

$$p(\mathbf{r}) = \begin{cases} X & 1 & \cos(\frac{2}{L}r) \\ = x_{iV,iZ} \end{cases}$$
 (19)

n can also be written in the matrix form :

$$_{n} = (V ^{y} P ^{(n)} V)_{nn} = v_{n}^{y} P ^{(n)} v_{n} ;$$
 (20)

where \mathbf{v}_n is the nth column of V , and

$$P_{ij}^{(n)} = h_{ij}^{*} \dot{p} (r R_{n}) j_{ji}^{*}$$
(21)

with j^{\sim} > being the set of partially occupied W annier functions obtained by maxim ization of . M atrix element P⁽ⁿ⁾ are calculated only once and stored for everyn. The minimum of n is obtained when u_n is equal to the normalized eigenvector corresponding to the smallest eigenvalue of P⁽ⁿ⁾. If we need several NOW AOs for a single atom ic site, the corresponding number of smallest eigenvectors should be chosen. The number of anti-bonding states necessary for the localization (L in eq.(10) can now be com puted by the following form ula:

$$L = N_A N_{LE} \qquad M ; \qquad (22)$$

where N_A is the number of atoms in the system and $N_L E$ is the number of the lowest eigenstates included into M ortensen-Parrinello localization. For example, for gold atom, which is typical electrode m aterial in m olecular electronics, ved-type and one s-type NOW AOs per atom are need. In Fig. 2, we plot the generated six NOW AOs for a gold atom in a simple gold wire junction system. We can clearly see that these six NOW AOs re ect the s and d characters of gold atom.

C. Conductance Form ula

The starting point for the conductance calculations is the Landauer form $\mathrm{ula^{19}}$

$$G = \frac{2e^2}{h}T (E_F);$$
 (23)

where T is the transm ission function and E_F is the Ferm i energy of the electrodes. Having obtained the partitioned Ham iltonian (5), we can compute transm ission as the trace of G reen's function G and coupling matrices L_{R} ?

$$T(E) = Tr[_{L}(E)G(E)_{R}(E)G^{Y}(E)]$$
: (24)

The matrices G and $_{L=R}$ are expressed by the matrix blocks of the H am iltonian H , overlap S , self energy :

$$G(E) = [E S_W H_W L_R]^{\perp}$$
(25)

and

$$L_{R} (E) = i \begin{bmatrix} & y \\ L = R & & L = R \end{bmatrix}$$
: (26)

The self-energies $_{L=R}$ are de ned via the G reen's function of the left and right electrodes g and the electrodew ire interactions:

$$_{L=R}$$
 (E) = (27)

(E
$$S_{W L=R}$$
 H $_{W L=R}$) $g_{L=R}$ (E) (E $S_{W L=R}^{Y}$ H $_{W L=R}^{Y}$):

It is not possible to include the entire leads in the practical calculations. The interaction between the wire and the in nitely large leads is accounted by the self-energy. Di erent theoretical models have been proposed to obtain q. The most accurate schemes relay on the surface G reen's function method. Even with some special techniques, such as transfer ${\tt m} \; {\tt atrix}^{20,21}$ and decim ation technique²², the computation of surface G reen's function is complex and time-consuming. Since detailed experin ental geom etrical structures of leads and a nanow ire are unclear in m ost cases, it enables us to use the simpler m odels for the leads. In this paper, the electrode is represented by a metal cluster with additional energy level broadening²³. This model has proven to be very successful in estimation of the bulk density of states from small cluster calculations.^{24,25} As shown in APPENDIX A, the Lorentzian broadening in the electrode density of state is the same as is positive in nitesimal in the electrode G reen's function:

$$g = [(E + i)S_{L=R} \quad H_{L=R}]^{1}$$
: (28)

III. TEST RESULTS

A. Computationalmethods

To illustrate the perform ance of our m ethod we com puted transport properties of N a nanow ire. N anow ires of m etal atom s have recently attracted m uch attention because of their fundam ental and technological importance. In particular, sodium atom ic wire has been studied both experimentally^{26,27,28} and theoretically.^{29,30,31,32,33} It was found that the conductance of N a wires exhibits even-odd oscillation as a function of the number of atom s in the wire. The conductance for odd sodium atom num – bered wire is close to the quantum of conductance G₀ ($2e^2=h$), while the conductance for even sodium atom num bered wires is sm aller than G₀. D i erent implementation and junction models lead to di erent the values of the conductance for even num bered nanow ires (0.5 { 0.9 G₀).^{29,30,31,32,33} W e use N a atom ic nanow ire as a proving ground for our implementation and we aim to reproduce the odd-even oscillation and values of the conductance.

The calculations were perform ed using our im plem entation of the formalism presented here in the CPMD package¹⁴. All systems were treated employing periodic boundary conditions and the KS orbitals were expanded in plane waves (50 Ry cuto) at the point of the Brilbuin zone. We used local density approximation for the exchange and correlation functional and Stum pf, G onze, and Schettlerpseudopotentials³⁴ for core electrons. The system is simulated by a cluster in a large supercell. The size of supercell is chosen in such a way that the distance between the nearest atoms in the neighboring cells is larger than 8.5A, so that the interaction between supercell in ages is negligible. An extensive set of the KS virtual orbitals is computed via Lanczos diagonalization³⁵ to ensure that all possible unoccupied anti-bonding states are included. To speed up convergence of the self-consistent iterations, free energy functional³⁶ is used with the electronic tem perature T = 300 K. Since sodium is a single valent atom, only one NOWAO per Na atom is constructed from the KS orbitals.

The whole system is divided into three parts: left electrode, central wire, and right electrode. The electrode part is obtained by cutting a few atoms from Na (001) surface. In particular, as shown in the inset of Fig. 3, we cut a ve-atom cluster, which is composed of square four-atom base and apex atom. The geometry of this ve-atom cluster is xed to the bulk values. The wire part is a single chain of N a atom s, where the distance between the atom s is constrained to the nearest neighbor distance in the bulk system. The distance between the electrode part and the wire part is optim ized. The optim ized value d is listed in Table I and it shows sm all

0:1 0:2 A odd-even oscillation as the length of the wire varies. We use optimized value of electrode-wire separation in all our calculations.

Let us take a three-atom Na wire as an example to illustrate conductance calculations by the m ethod we described in the previous section.

First, electronic structure of the whole system is calculated, and a set of KS orbitals is obtained. The number of KS orbitals should be large enough to include all unoccupied anti-bonding states. Fig.3 shows the conductance

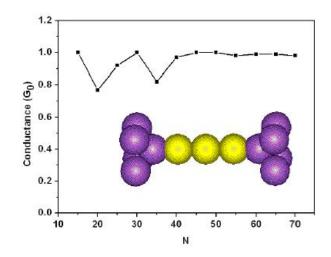


FIG.3: Conductance of three-atom N a atom ic wire as a function of number of K ohn-Sham orbitals calculated to construct the NOW AOs. The inset shows the geometry of this junction system .

as a function of the number of KS orbitals included in the localization procedure to de ne NOW AOs. The deviation of the conductance from the correct value $(I G_0)$ vanishes rapidly as the number of virtual KS orbitals is increased. Our test calculations illustrate the number of the virtual KS orbitals can be adjusted to achieve any desired level of accuracy in the conductance calculations. The results on Fig.3 demonstrate that 45 virtual KS orbitals are su cient to get the converged result for three atom Nawire.

Second, this set of KS orbitals is used to construct NOW AOs, with which Ham iltonian matrix H and overlap matrix S are calculated. By solving the corresponding generalized eigenvalue problem, we get a set of energy levels for the whole junction system, as shown in the left column of Fig. 1c. The di erences between these eigenlevels and the Kohn-Sham energies are very small, especially for occupied state. At the same time, partition of H and S is in plem ented, and the energy levels of electrodes, $^{\rm L}$ and $^{\rm R}$, are obtained by solving the generalized eigenvalue problem for the corresponding submatrices.

Third, we introduce Lorentzian broadening of the left and right energy levels to continuous density of states, to compute the self-energy matrices. The broadening param eter is chosen to be 0.025 H artree here, and the effect of broadening param eter on conductance will be discussed later. The transmission probability is computed by using section IIB equations. The peak positions of the transmission curve can be considered as renorm alized eigen levels of the central three-atom N a wire coupled to the electrodes (C in Fig. 1).

In units of G_0 , the conductance equals to the value of the transm ission at Ferm i energy of the leads. Ferm i energy for the electrode is not known apriori and it has to be computed within the approach. There are two schem es to com pute Ferm i energy of the electrodes. The

rst one determ ines the Ferm i energy at which the integrated density of states should be equal to the number of electrons in the electrode cluster.²³ The charge population of the electrode cluster is calculated by $_{L=R} = P_{12\,L=R} (S^{1=2}P S^{1=2})_{ii}$, where P is the density matrix on NOW AOs basis set, which is obtained from the generalized eigenvalue problem of the whole junction cluster system. The other one is more simple, we can just use the Ferm ienergy of the whole junction system. When the electrode clusters are very large, both methods become equivalent. For the ve-atom model used here, we nd the later method is preferable and it yields 1 G₀ value of the conductance of the three-atom N a wire system.

B. O scillation of C onductance

The most important feature of electronic current ow through Na atom ic wires is that the conductance oscillates as a function of the number of atoms in the wire We calculate the conductance of Na atom ic wires with length range from 2 to 5 atoms. The odd-even oscillation of the conductance is well reproduced as shown in Fig. 4a. The conductance for N = 3 and N = 5 is one unit conductance G_{0} , while the conductance for N = 2and N = 4 is about 0.7 G $_0$. The transmission curves for these wire systems are plotted in Fig. 4b. We can see that the number of sharp peaks in the transmission curves, i.e. the number of resonant states, is equal to the number of atoms in the wire. The low temperature transport properties are mainly determ ined by the states near the Ferm i energy. There is a resonant state at the Ferm i energy for odd num bered Na wires, but there is no such state for even numbered Nawires. This is exactly the reason of the even-odd oscillation behavior of the conductance.^{30,32}

C. Eigenchannels

Since there are multiple peaks in the transmission curve, it is interesting to see if sodium wires are single channel conductor as we expected form onovalent atom ic chain. By de ning

$$t = {1 \over L} G^{R} {R \over R} {1 \over 2}$$
 (29)

the transm ission can be written as T (E) = Tr(tt^y). We can decompose the transm ission to the combination of some eigenchannels diagonalizing the matrix tt^{y} .³⁷ For sodium wires, we get only one non-zero eigenvalues at any energy, which is the manifestation of a single channel conduction mechanism.

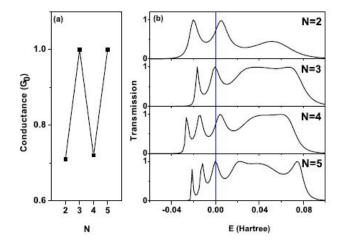


FIG. 4: (a) C onductance oscillation of sodium atom ic wire with its length. (b) T ransm ission curves of the sodium atom ic wires. Ferm i energy is set to zero.

TABLE I:D istance between electrode and wire d (in A), and conductance of the N a atom ic wire junction systems. The length of N a wire N ranges from 2 to 5 atom s. The electrode part of the junction system is modeled by one (E1 model) or ve (E5 model) N a atom s. Conductance for four di erent broadening param eter 0.02, 0.025, 0.03, and 0.04 H artree are listed. See text for more details.

	E1M odel					E5M odel				
Ν	d	0.02	0.025	0.03	0.04	d	0.02	0.025	0.03	0.04
2	3.004	0.33	0.43	0.50	0.57	3.078	0.64	0.71	0.75	0.77
3	3.070	0.99	0.99	0.98	0 . 97	3.270	0.99	1.00	1.00	0.99
4	3.024	0.65	0.81	0.92	1.00	3.097	0.71	0.72	0.72	0.69
5	3.042	0.99	0.99	0.99	0.99	3,221	1.00	1.00	0.98	0.96

D. Electrode Cluster M odel

In our method, the electrode is approximated by a small cluster with proper level broadening. Therefore it is important to understand how the results of our calculations are a ected by the cluster size and by the choice of the broadening.

The size of the electrode cluster should be big enough, so that charge neutrality is maintained for the junction system. As it was discussed in the sections IIIA and IIIB the ve-atom electrode model is su cient to simulate the transport behavior of sodium wires in our method.³⁸ It is already a very small size comparing to typically used models for electrodes, but it is interesting to see if a smaller cluster still works in our method. For this purpose, we also check the simplest one-atom model. The results are listed in Table I. Comparing to the ve-atom model, the oscillation strength of the optim ized distance between electrode and wire is smaller. W e can see that the conductance for one-atom model still exhibits the even-odd oscillation, but the conductance of even numbered wires are not very stable anymore. This result indicates that the one-atom electrode model provides the oversimpli ed description of the system.

It is also in portant to test if the broadening param eter strongly e ects results of the transport calculations. We analyzed the conductances for all wires by varying the broadening param eter from from 0.02 to 0.04 H atree, and list the result in Table I. We nd that for large electrode m odel, the conductance is not very sensitive to the variations of , especially for odd-num bered wire system. For one-atom electrode m odel, the conductance changes signi cantly as varies. This is because there is only one electrode energy level for one-atom m odel, and the shape of the density of states at $E_{\rm F}$ strongly depends on the broadening param eter.

There is another conductance calculation method for single channel nanow ire.^{30,39} It is based on Friedel sum rule and also relays on the eigenlevel broadening technique to represent continuum of states in the contact. In that method, the eigenvalues of the whole junction sysare broadened to obtain density of states, thus the tem broadening parameter should be smaller than the resonance spacing but larger than single particle level spacing for electrode. To satisfy this constraint, the spacing of ^L and _R should be much smaller than that of C , and therefore much larger electrode clusters should be used in Friedel sum rule based calculations. In our method, how ever, if the broadening parameter is comparable to the resonance spacing, we still get very accurate results. Therefore, much smaller metal clusters can be used to m odel electrodes within our im plem entation.

IV. CONCLUSIONS

We have developed and implemented a plane wave based method to calculate the conductance of nanostructures. The fundamental quantity in the present in plementation is NOWAOs which are obtained by the multi-step localization of KS orbitals. NOWAOs are used to partition KS H amiltonian to electrode wire electrode submatrices that is necessary step for the G reen's function based conductance calculations. The electrode parts are modeled by small clusters with proper broadening of their eigenlevels and this model is especially suitable for systems with very limited knowledge of lead-wire bonding structure. Transport properties of sodium nanowires are studied by this method and the odd-even oscillations of the conductance are reproduced.

A cknow ledgm ents

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APPENDIX A:LORENTZIAN BROADENING OF ELECTRODES LEVELS

The density of states of the leads is related to im aginary part of G reen's function by

$$\operatorname{Im} g(E) = D(E) \qquad (A1)$$

and real part of G reen's function can then be obtained by K ram ers-K oning relation

$$\operatorname{Reg}(E) = \frac{1}{-P} \frac{\sum_{i=1}^{Z} \frac{1}{i}}{\frac{\operatorname{Im} g(!)}{!}} \frac{\operatorname{Im} g(!)}{!} d! : \quad (A2)$$

Here P stands for the Cauchy principal value integral. For the widely used Gaussian broadening,²³ this procedure is num erically complicated (Romberg integration technique) and time-consuming. We use the Lorentzian broadening instead and we will show in this appendix that the broadening parameter in Lorentzian for the density of states is the same as the in nitesimal parameter in the non-interacting electrode G reen's function. The Lorentzian broadening function is written as

D (E) =
$$\frac{1}{a} \frac{X}{(E_{i})^{2} + a^{2}}$$
; (A3)

where $_{\rm i}$ are the eigenlevels for the left or right electrode cluster. The Cauchy principal integral can be obtained analytically for the Lorentzian density of states and it yields the following G reen's function matrix for the leads

$$g_{ij}(E) = \frac{ij}{(E_{i})^2 + 2}(E_{i} i)$$
 (A4)

or in matrix form

$$g(E) = \frac{ij}{(E + i)^2 + 2} (E + i)$$

$$= [(E + i)I + 1]^{-1} : (A5)$$

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